

- Drafts
  - BRS:
  - BRS:
  - BRS:
  - BRS: Knall
  - BRS: 19 21 23
  - BRS: 32 with 33
- Pending
- Active
  - (43) ((bird adj beak) and ((sonos monos mnos))) and ((charge ne

Failed

Saved

- S1: (1) 09/648877
- S2: (1736) "KONINKLIJKE PHILIPS" as.
- S3: (0) 10/753914
- S4: (4) 20030109083 "6,670,671 pn."
- S5: (1) 10/716703
- S6: (326209) (sonos monos)
- S7: (317007) (sonos monos mnos)
- S8: (9493) (charge near3 (strap\$4 trap\$4 nitride))
- S9: (116408) "F" bsm.
- S10: (103597) bl bitline bit adj line readline read adj line sense adj line
- S11: (506600) (wordline "W1" ( word digit control adj gate) adj line) (wo
- S12: (40497) (tl bidline bit adj line readline read adj line sense adj line)

(((bird adj beak)  
)) and (((sonos monos mnos)  
)) and ((charge near3 (strap\$4 trap\$4 nitride))  
)

Feb. 2005

U	Inventor	Document/Issue P	Title	Current	Current X	Retrieval	S	C	P	S	S	Image	Do	P
1	Ramsey, US 654161 2003 2	Planar structure for non-volatile memo	257/32 257/E21.6										US 654161	
2	Yoshino, A US 200401 2004 2	Nonvolatile semiconductor memory de	257/31										US 200401	
3	Lee, Chang US 20050 2005 2	Nonvolatile memory devices and meth	438/25 438/265										US 20050	
4	Moriya, Hir US 200500 2005 2	NON-VOLATILE SEMICONDUCTOR M	438/26										US 20050	
5	Lee, Chang US 200301 2003 2	Nonvolatile memory devices and meth	365/20 257/E21.6										US 200301	
6	Tori, Satos US 200300 2003 4	Non-volatile semiconductor memory a	257/31 257/E21.6										US 200300	
7														
8	Moriya, Hir US 200300 2003 2	Nonvolatile semiconductor storage de	365/20 257/E21.8										US 200300	
9	Lee, Chang US 200300 2003 1	Method of forming non-volatile mem	438/25										US 200300	
10	Goda, Aki US 200300 2003 1	Semiconductor device and method of	257/149 257/E21.5										US 200300	
	Ramsey, US 200201 2002 2	Simultaneous formation of charge stor	438/25 257/E21.6										US 200201	

[Total: 100 items]

100